



(2-92)

Sheet 1 of 1

Form PTO-1449 <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b> (Use several sheets if necessary)				Docket Number (Optional) 3255.1US (91-507.1-RE)		Application Number 09/488,099	
				Applicant <b>Dennison et al.</b>			
				Filing Date <b>January 18, 2000</b>		Group Art Unit <b>2822</b>	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
W	4,617,193	10/1986	Wu				
	4,714,686	12/1987	Sander et al.				
	4,868,138	09/1989	Chan et al.				
	4,892,845	01/1990	Bridges				
	5,110,766	05/1992	Maeda et al.				
	5,124,280	06/1992	Wei et al.				
	5,158,910	10/1992	Cooper et al.				
W	5,171,713	12/1992	Matthews				
<b>FOREIGN PATENT DOCUMENTS</b>							
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES NO	
W	41 07 883	09/1991	DE			X	
W	62-32630	02/1987	JP			X	
W	64-72543	03/1989	JP			X	
<b>OTHER DOCUMENTS</b> (Including Author, Title, Date, Pertinent Pages, Etc.)							
W		Yoshire Nakata et al., "Tunnel Shape Stacked Capacitor (TSSC) Memory Cell for 64Mb Dram", article (date unknown).					
EXAMINER <i>W. P. ...</i>				DATE CONSIDERED 3/30/05			
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.							

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